

ABSTRACT

The present invention provides a chamber cleaning gas for Si film, SiO_2 film, Si_3N_4 film or high-melting metal silicate film, the gas comprising at least one gas selected from the group consisting of $\text{CF}_3\text{CF}=\text{CF}_2$,
5 $\text{CF}_3\text{CF}-\text{CF}_2$ and $\text{CF}_3\text{C}=\text{O}$, and provides a chamber cleaning method.

$\text{CF}_3\text{CF}-\text{CF}_2$ $\text{CF}_3\text{C}=\text{O}$

O |
 CF₃